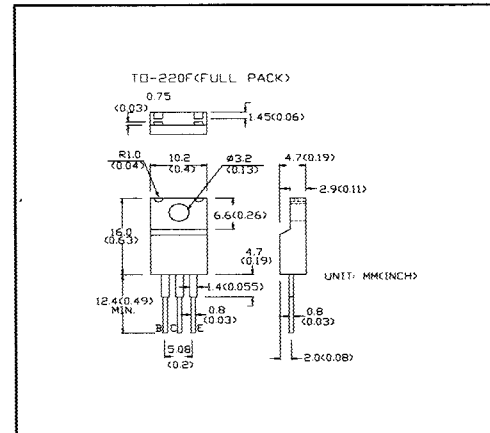


MICRO ELECTRONICS

CL2102
NPN
SILICON
TRANSISTOR

DESCRIPTION

CL2102 is planar transistor use for in AF medium power drivers and outputs and switching applications.



ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	120V
Collector-Emitter Voltage	VCEO	65V
Emitter-Base Voltage	VEBO	7V
Collector Current	IC	1A
Total Power Dissipation	Ptot	1W
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	120		V	IC=0.1mA IE=0
Collector-Emitter Breakdown Voltage	LVCEO*	65			IC=10mA IB=0
Emitter-Base Breakdown Voltage	BVEBO	7			IC=0.1mA IC=0
Collector Cutoff Current	ICBO		2		VCB=60V IE=0
Emitter Cutoff Current	IEBO		5		VEB=5V IC=0
D.C. Current Gain	HFE*	20			IC=0.1mA VCE=10V
		35			IC=10mA VCE=10V
		40	120		IC=150mA VCE=10V
		25			IC=500mA VCE=10V
		10			IC=1A VCE=10V
Collector-Emitter Saturation Voltage	VCE(sat)*		0.5	V	IC=150mA IB=15mA
Base-Emitter Saturation Voltage	VBE(sat)*		1.1	V	IC=150mA IB=15mA
Gain Bandwidth Product	fT	60		MHz	IC=50mA VCE=10V f=20MHz
Output Capacitance	Cob		10	pF	VCB=10V f=1MHz
Input Capacitance	Cib		80	pF	VEB=0.5V f=1MHz

* Pulse test : pulse width <300μS, duty cycle < 2%.



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